

TRANSISTOR(PNP)

FEATURES

Power dissipation

MAXIMUM RATINGS(TA=25°C unless otherwise noted)

Symbol	Parameter	Value	Units
V _{CBO}	Collector-Base Voltage	-50	V
V _{CEO}	Collector-Emitter Voltage	-50	V
V _{EBO}	Emitter-Base Voltage	-5	V
I _C	Collector Current-Continuous	-0.15	A
P _D	Collector Power Dissipation	0.4	W
T _J	Junction Temperature	150	°C
T _{Stg}	Storage Temperature	-55-150	°C

ELECTRICAL CHARACTERISTICS(Ta=25°C unless otherwise specified):

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	V _{(BR)CBO}	IC=-100uA, IE=0	-50			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	IC=-1mA, IB=0	-50			V
Emitter-base breakdown voltage	V _{(BR)EBO}	IC=-100uA, IC=0	-5			V
Collector cut-off current	I _{CBO}	V _{CB} =-50V, IE=0			-100	nA
Collector cut-off current	I _{CEO}	V _{CE} =-50V, IB=0			-100	nA
Emitter cut-off current	I _{EBO}	V _{EB} =-5V, IC=0			-100	nA
DC current gain	H _{FE(1)}	V _{CE} =-6V, IC=-2mA	70		400	
	H _{FE(2)}	V _{CE} =-6V, IC=-150mA	25			
Collector-emitter saturation voltage	V _{CE(sat)}	IC=-100mA, IB=-10mA			-0.3	V
Base-emitter saturation voltage	V _{BE(sat)}	IC=-100mA, IB=-10mA			-1.1	V
Gain Bandwidth Product	f _T	V _{CE} =-10V, IC=-1mA, f=30MHz	80			MHz
Collector output capacitance	C _{ob}	V _{CB} =-10V, IE=0, f=1MHz			7	pF
Noise figure	NF	V _{CE} =-6V, IC=-0.1mA, f=1KHz RG=10KΩ			6	dB

CLASSIFICATION OF H_{FE(1)}

RANK	O	Y	GR
RANGE	70-140	120-240	200-400

Typical Characteristics

